



CST90P03F P-Ch 30V Fast Switching MOSFETs

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

CST90P03F Product Summary



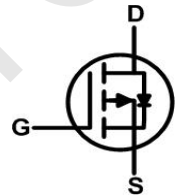
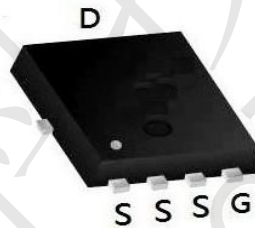
BVDSS	RDSON	ID
-30V	3.5mΩ	-90 A

CST90P03F PRPAK5X6 Pin Configuration

CST90P03F Description

The CST90P03F is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The CST90P03F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.



CST90P03F Absolute Maximum Ratings (T_A= 25°C, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _C =25°C	I _D	-90	A
	T _C =100°C		-57	
Pulsed Drain Current ¹		I _{DM}	-360	A
Single Pulse Avalanche Energy ²		EAS	125	mJ
Total Power Dissipation	T _C =25°C	P _D	60	W
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	R _{θJA}	55	°C/W
Thermal Resistance from Junction-to-Case	R _{θJC}	2.08	°C/W



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CST90P03F Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	-	-	V	
Gate-body Leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V	T _J =25°C	-	-	-1	μA
			T _J =100°C	-	-	-100	
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V	
Drain-Source On-Resistance ⁴	R _{DS(on)}	V _{GS} = -10V, I _D = -30A	-	3.5	4.5	mΩ	
		V _{GS} = -4.5V, I _D = -15A	-	4.8	6.2		
Forward Transconductance ⁴	g _{fs}	V _{DS} = -10V, I _D = -30A	-	90	-	S	
Dynamic Characteristics⁵							
Input Capacitance	C _{iss}	V _{DS} = -15V, V _{GS} = 0V, f = 1MHz	-	5070	-	pF	
Output Capacitance	C _{oss}		-	695	-		
Reverse Transfer Capacitance	C _{rss}		-	580	-		
Gate resistance	R _g	f = 1MHz	-	4	-	Ω	
Switching Characteristics⁵							
Total Gate Charge	Q _g	V _{GS} = -10V, V _{DS} = -15V, I _D = -30A	-	146	-	nC	
Gate-Source Charge	Q _{gs}		-	21.5	-		
Gate-Drain Charge	Q _{gd}		-	39	-		
Turn-On Delay Time	t _{d(on)}	V _{GS} = -10V, V _{DD} = -15V, R _G = 3Ω, I _D = -30A	-	23	-	ns	
Rise Time	t _r		-	15	-		
Turn-Off Delay Time	t _{d(off)}		-	129	-		
Fall Time	t _f		-	28	-		
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴	V _{SD}	I _S = -30A, V _{GS} = 0V	-	-	-1.2	V	
Continuous Source Current	I _S	T _C =25°C	-	-	-90	A	

Note :

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C
2. The EAS data shows Max. rating . The test condition is V_{DD}= -25V, V_{GS}= -10V, L= 0.1mH, I_{AS}= -50A
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.



CST90P03F Typical Characteristics

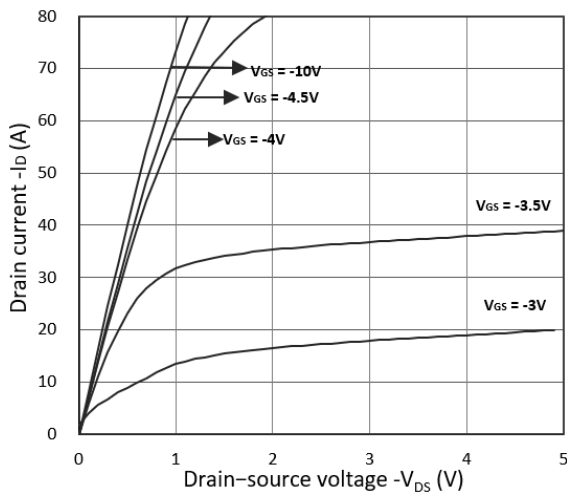


Figure 1. Output Characteristics

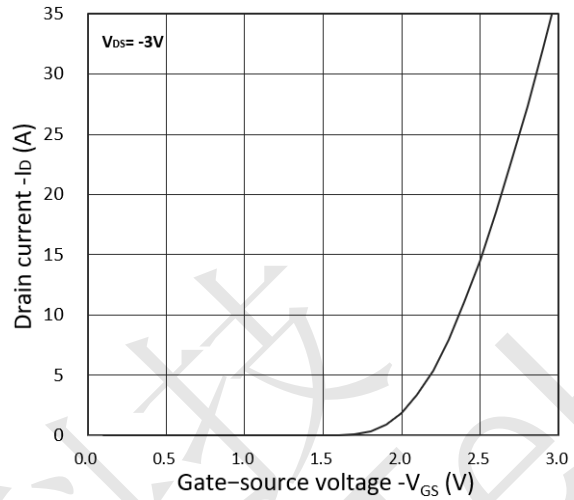


Figure 2. Transfer Characteristics

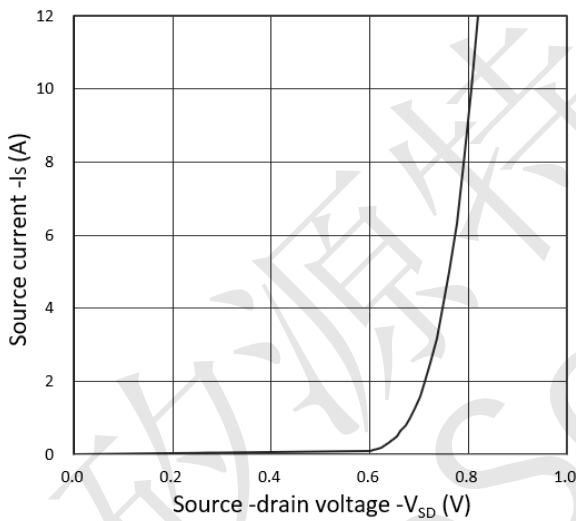


Figure 3. Forward Characteristics of Reverse

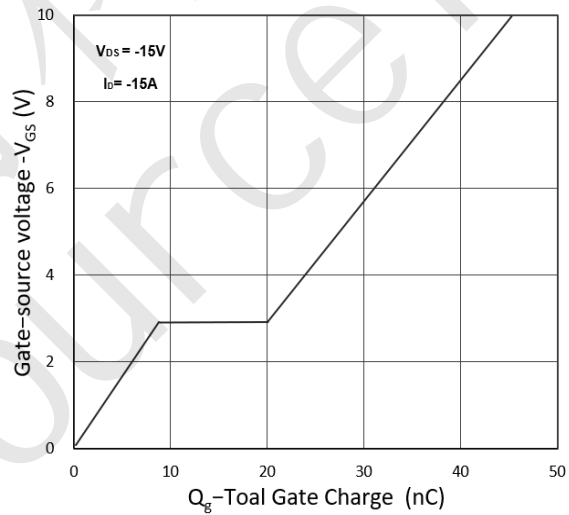


Figure 4. Gate Charge Characteristics

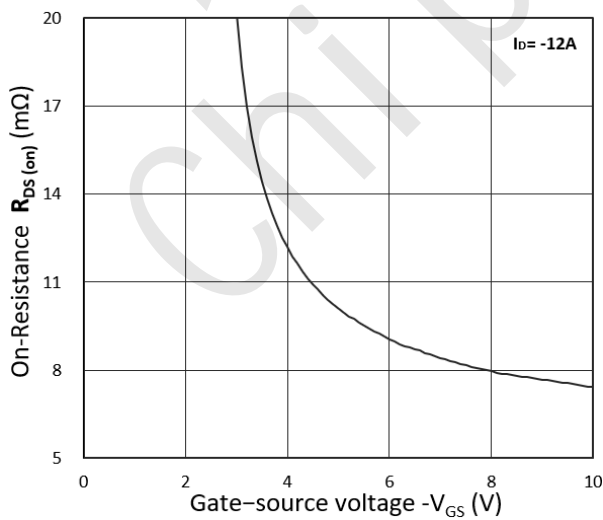


Figure 5. $R_{DS(on)}$ vs. V_{GS}

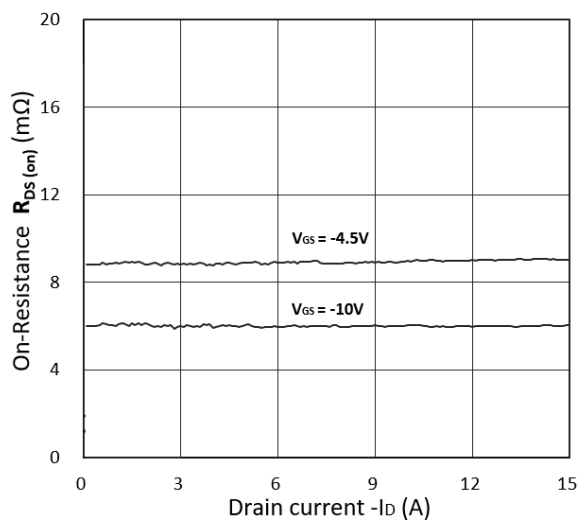


Figure 6. $R_{DS(on)}$ vs. I_D



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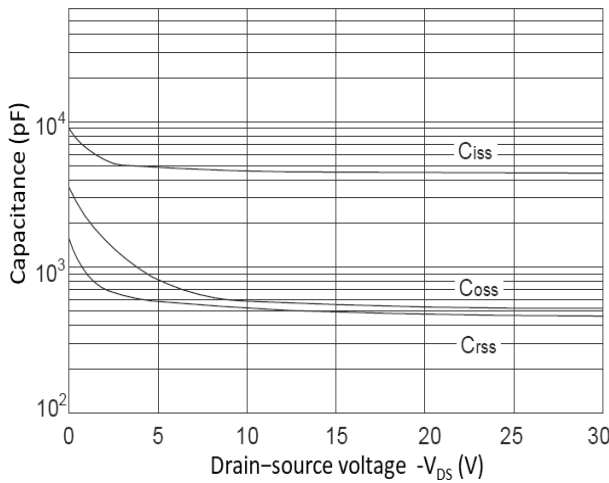


Figure 7. Capacitance Characteristics

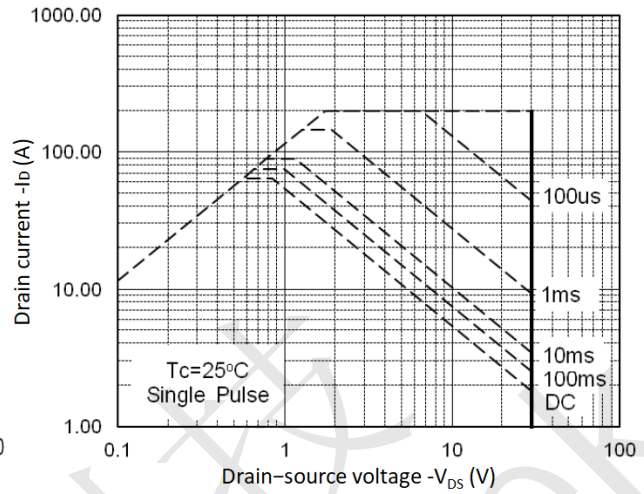


Figure 8. Safe Operating Area

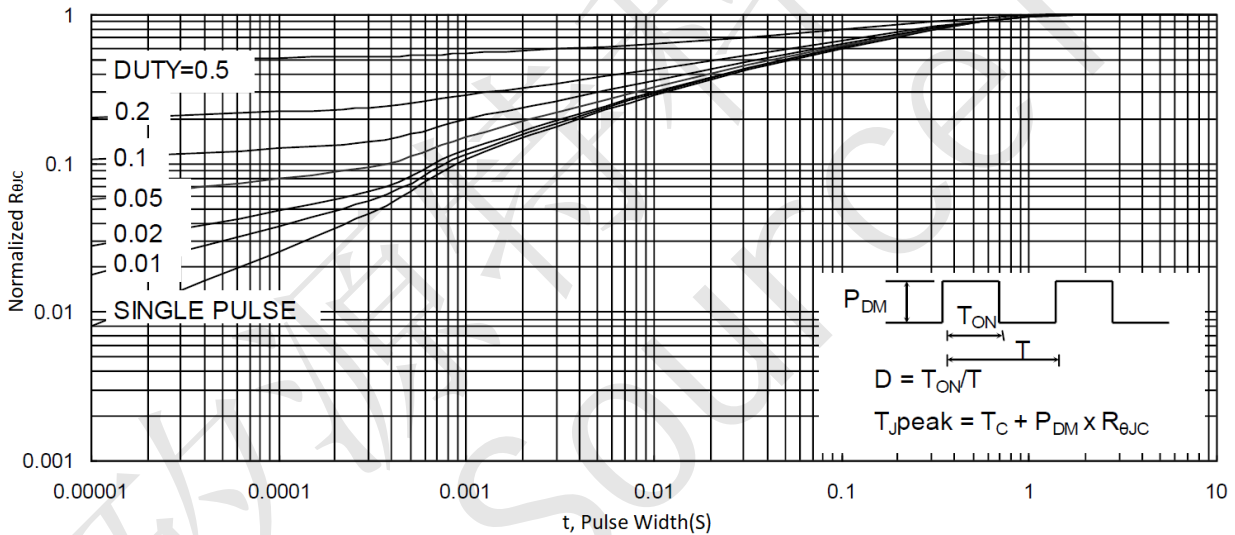


Figure 9. Normalized Maximum Transient Thermal Impedance

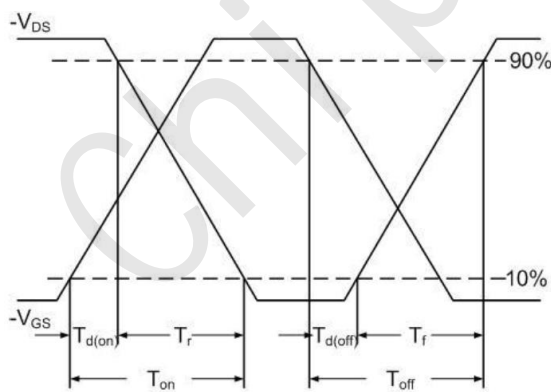


Figure 10. Switching Time Waveform

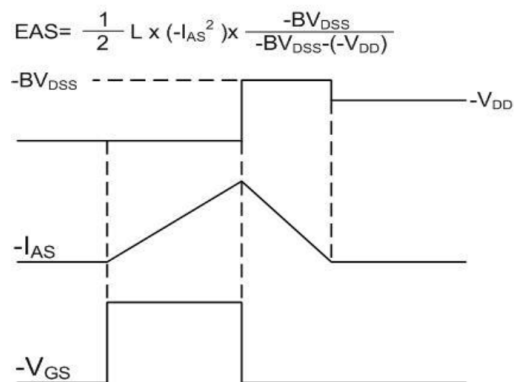


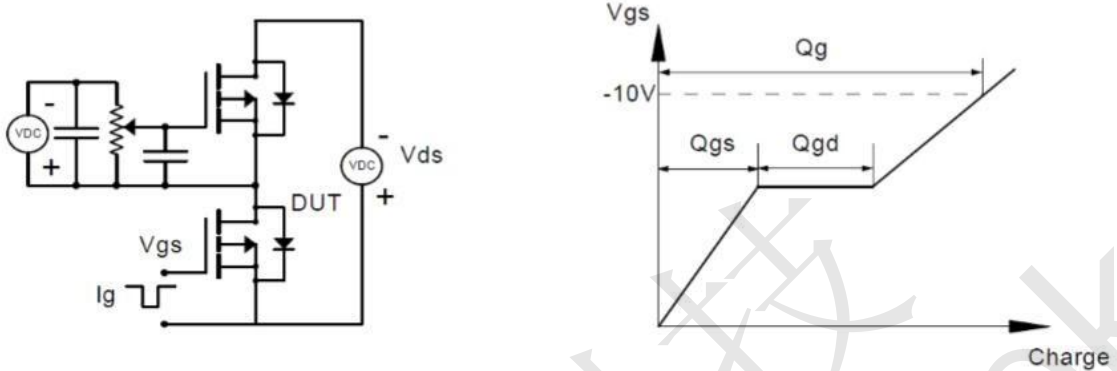
Figure 11. Unclamped Inductive Switching Waveform



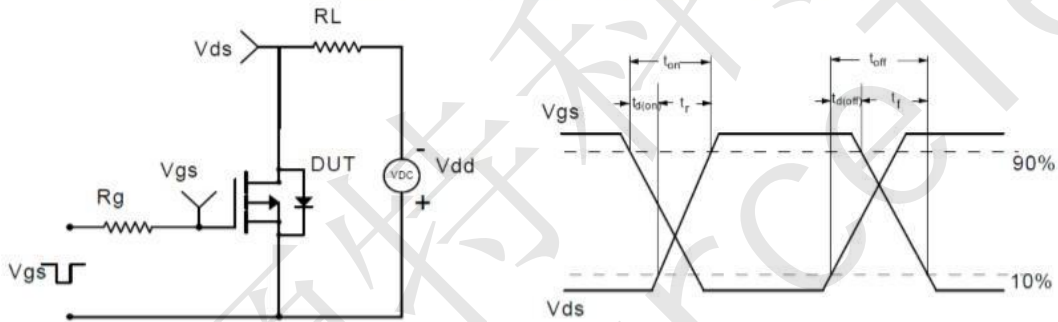
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CST90P03F Test Circuit

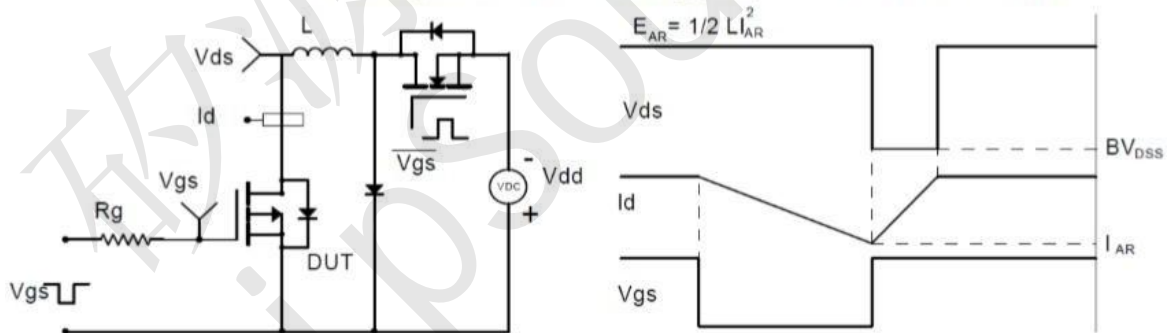
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

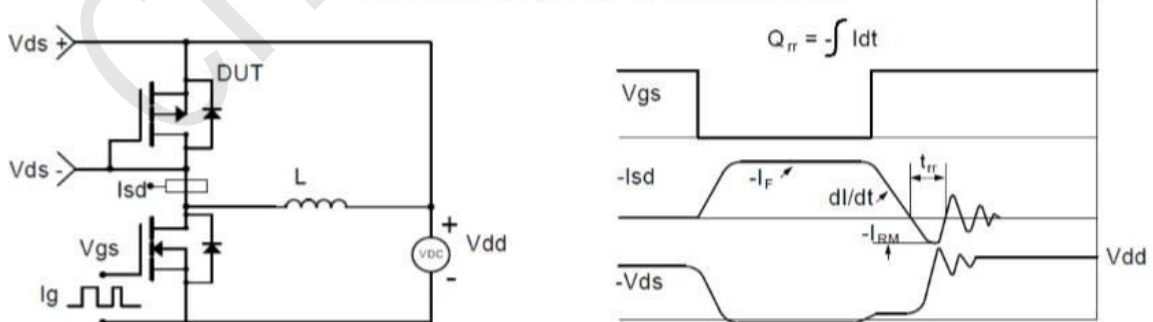
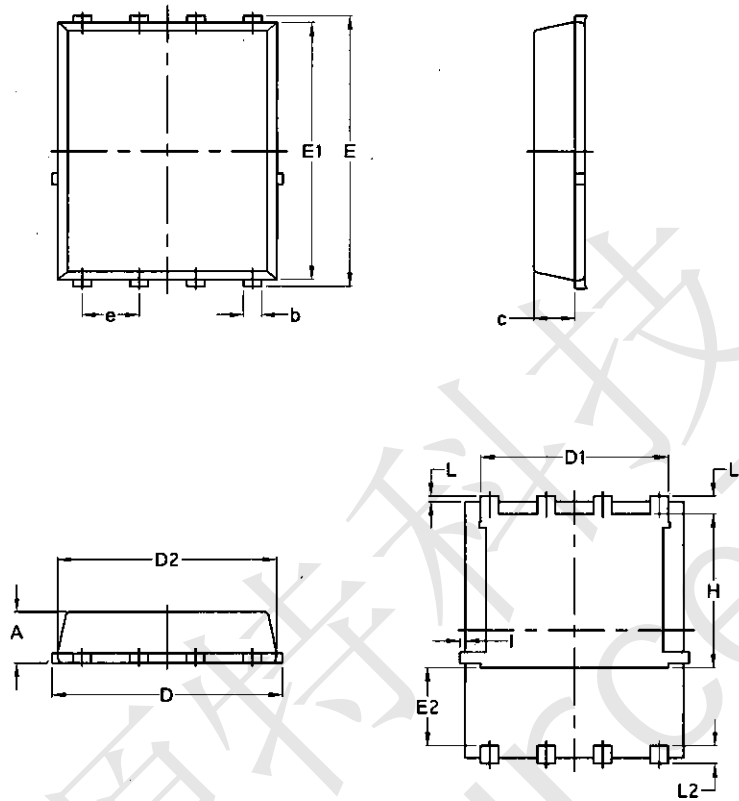


Figure C. Unclamped Inductive Switching Circuit & Waveforms



CST90P03F P-Ch 30V Fast Switching MOSFETs

CST90P03F Package Mechanical Data-DFN5*6-8L-Single



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070